



Optical and structural properties of 2D transition metal dichalcogenides semiconductor MoS₂

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Abstract. Two-dimensional molybdenum sulphide (MoS₂) has been synthesized by hydrothermal method, and for optical characteristics, absorption and photoluminescence spectra are recorded. Variation of refractive index, extinction coefficient, dielectric constant (both real and imaginary) and optical conductivity with wavelength have been plotted. The exciton energy has been calculated in the weak electron–phonon coupling regime. The temperature-dependent splitting energy of valance band is well explained by using simulation. Splitting energy is constant up to 50 K and then decreases with increase in temperature. Average lifetime (0.75 ns) of excited electrons have been calculated using time-correlated single photon counting. X-ray diffraction (XRD), Raman spectra and high-resolution transmission electron microscope (HRTEM) have been recorded to investigate structural properties of MoS₂ sample. XRD shows hexagonal crystal symmetry with well-defined crystallinity. In Raman spectra, three prominent peaks are found at 381, 407 and 453 cm⁻¹. HRTEM also confirms that the structure of MoS₂ is hexagonal with three layers of nano-sheet with inter-planer spacing of 0.58 nm

Keywords. Molybdenum sulphide; dielectric constant; splitting energy; photocatalytic activity; nano flake; exciton energy.

1. Introduction

Recently, many researchers have investigated on semiconducting nanomaterials due to their potential properties (optical, electronic, catalytic, etc.) and powerful applications in different branches, such as solar cell, photo detector, photocatalytic, energy storage, optoelectronic device, etc. [1–4]. The optical and electronic properties of semiconducting materials are dealt with the different applications. The efficiency of the activity has also been increased due to enhanced optical and electronic properties [3,5]. Among the semiconductor materials, two-dimensional transition metal dichalcogenide semiconductors (TMDCs) have tunable optical properties to make application in devices [6–8].

Layered structure transition metal dichalcogenide semiconductors has co-valent bond in-plane and weak Van der wall's force out-of-plane [9]. Due to this layered structure of TMDCs, bandgap energy and optical and electronic properties can be tuned by decreasing number of layers [10]. Among all TMDCs, MoS₂ is attractive semiconductor due to its remarkable optical, electronic and catalytic properties and has wide range of applications in different field of solar cells, gas sensor, energy storage, photocatalysis, etc. [11–14]. MoS₂ has a direct and indirect bandgap of

1.9 and 1.2 eV for mono layer and bulk materials, respectively, due to quantum confinement [15].

Different methods like mechanical exfoliation, chemical vapour deposition, hydrothermal, etc. have been investigated for synthesis of molybdenum sulphide (MoS₂). Feng *et al* [16] synthesized MoS₂ nano-flakes by rheological phase reaction method to investigate electrical properties. Wang *et al* [14] synthesized MoS₂ nanostructure for studying energy storage properties. Saha *et al* [17] prepared spherical amorphous MoS₂ by simple solvothermal decomposition for photocatalytic rose Bengal dye degradation. Luo *et al* [18] synthesized different types of morphology by hydrothermal method for photocatalytic application. In this work, MoS₂ nano-flakes have been synthesized by simple and convenient hydrothermal method to study optical and electronic properties.

Due to high demand for textile products, the use of synthetic dyes has been gradually increased and it releases large amount of dying waste, which pollutes both land and fresh water. Photocatalytic degradation is one of the convenient processes to treat waste water in a cost-effective way [19,20]. Here, photocatalytic effect of few-layered MoS₂ has been demonstrated by decomposing methylene blue (MB) dye in water solution under visible-light irradiation.

2. Experimental

2.1 Materials

To prepare MoS₂ nano-crystal, high-purity molybdenum trioxide (MoO₃) and potassium thiocyanate (KSCN) were purchased from Merck Life Science Private Limited. Also, sodium hydroxide (NaOH) and 35% hydrochloric acid (HCl), ethanol, methylene blue (MB) and double-distilled water were taken. All reagents were used without further purification.

2.2 Synthesis method

Molybdenum sulphide (MoS₂) nano-flakes have been grown using hydrothermal method. In this typical process, molybdenum trioxide (MoO₃) and potassium thiocyanate (KSCN) were used as molybdenum and sulker precursors, respectively. At first, 288 mg molybdenum trioxide and 388 mg potassium thiocyanate (1:2 molar ratio) were mixed with 40 ml double-distilled water via ultra-sonication for 60 min. To fix pH value 2.0, 1 mol l⁻¹ HCl solution was compiled and then mixed solution were stirred for 15 min with the magnetic stirrer. After that, the mixed solution was shifted into a 50 ml autoclave at 230°C for 30 h. Then it was cooled down normally to room temperature and centrifuged at 5000 rpm for 10 min. Finally, the prepared sample was washed several times with double-distilled water and ethanol to remove different ions, and it was kept in a vacuum desiccator at room temperature for 2 days for drying. Prepared powder sample was heated at 40°C for 6 h to remove any moisture in it.

2.3 Sample characterization

For investigation of optical properties of the prepared molybdenum sulphide (MoS₂), absorption spectra were recorded from 250 to 800 nm by using Carry 5000 UV-Vis NIR Spectrometer with scan rate 600 nm min⁻¹, photoluminescence (PL) spectra were recorded using Fluorescence Spectrophotometer, F-7000 (Hitachi High-Tech) and decay plot was investigated by Time-correlated single photon counting (TCSPC) system (HORIBA). To study the structural phase and electronic properties of prepared powder sample, Raman spectra were performed using Raman spectroscopy with an excitation wavelength of 532 nm. X-ray powder diffraction (XRD) data was performed in a RIGAKU X-ray diffractometer using Cu K α radiation ($\lambda = 1.5418 \text{ \AA}$) in the range 10° to 90° to study the crystallinity and structural information. High-resolution transmission electron microscope (HRTEM) was done by using JEOL JEM200 operating at 200 kV.

3. Results and discussion

3.1 UV-vis spectra of 2D material MoS₂

In order to investigate the optical property of prepared powder sample, UV-visible absorption spectra were taken at room temperature after dispersing in water, as shown in figure 1. The couple peaks for few-layered 2H-MoS₂ located at 673 and 624 nm in the absorption spectra can be attributed to A and B excitonic interband transition at the K-point of Brillouin zone [15]. The peaks originate due to spin-orbit splitting of valance band at K-point, which is depicted in figure 2c [17]. The C and D excitonic transitions from the deep valance to conduction band edge at M-point of Brillouin zone is the source of absorption peak at 460 and 396 nm in the spectra [21]. All of these features in figure 1 clarify few-layered 2H-MoS₂, as earlier reported for liquid-based exfoliation of monolayer MoS₂ from the bulk [22].

Due to quantum confinement, the bandgap energy increases with decrease in layer number. It can be well explained by using density function theory with generating electronic band structure and density of state (DOS; see figure 2). Here, $a = b = 0.316 \text{ nm}$ and $c = 1.226 \text{ nm}$ were used, which are calculated from XRD and HRTEM result and the calculations with spin-orbit interaction have been carried out using the density functional theory (DFT)-based CASTEP computer program together with the generalized gradient approximation (GGA) with the PBE exchange-correlation function [23]. The plane-wave basis set cut-off was set at 420 eV. The K-point sampling of the Brillouin zone was constructed using Monkhorst-Pack scheme with $9 \times 9 \times 1$ grids in bulk MoS₂. The equilibrium crystal structures were obtained via geometry optimization in the Broyden-Fletcher-Goldfarb-Shanno (BFGS) minimization scheme. In the geometry optimization, criteria of convergence were set to $1.0 \times 10^{-5} \text{ eV}$ per atom for energy, 0.03 eV \AA^{-1} for force, $1 \times 10^{-3} \text{ \AA}$ for ionic displacement, and

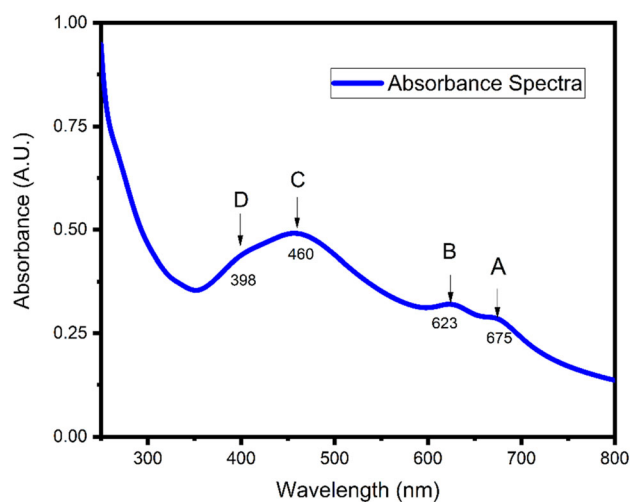


Figure 1. Absorption spectra of MoS₂.

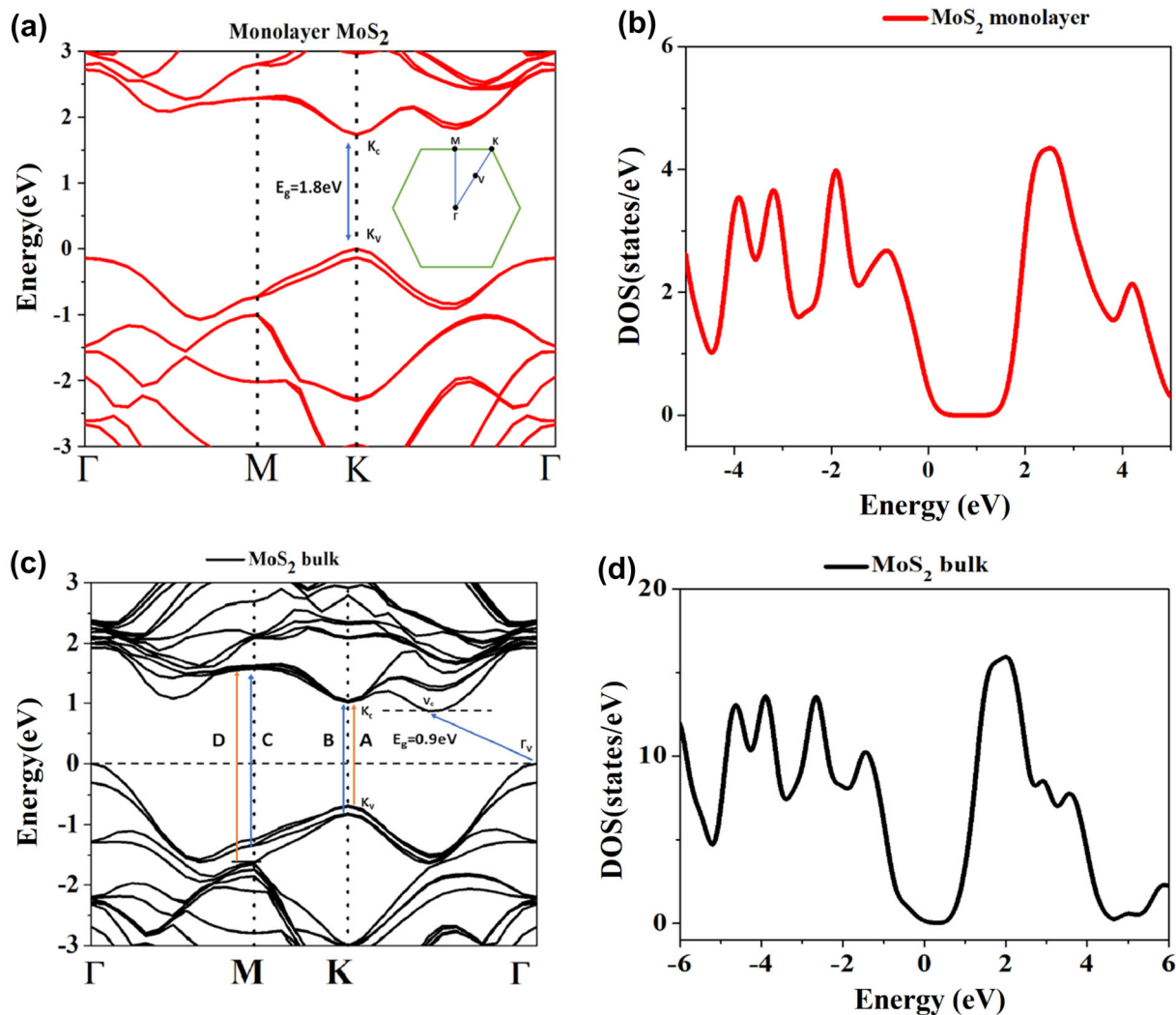


Figure 2. Electronic band structure for (a) monolayer MoS₂ and (c) bulk MoS₂. Density of state for (b) monolayer MoS₂ and (d) bulk MoS₂.

0.05 GPa for stress. These parameters are carefully tested and sufficient for a well converged total energy.

According to electronic band structure, the density of states, bandgap energy varies with the number of layers. The bandgaps are 0.9 and 1.8 eV for bulk and monolayer MoS₂, respectively (which is significantly smaller than the experimental value 1.2 eV and 1.9 eV). Yokovkin [24] reported bandgap energy of 0.76 and 1.84 eV for bulk and monolayer MoS₂, respectively, by calculating band structure. In the band structure, few-layered MoS₂ has an indirect transition between Γ_v (valenced band maxima (VBM) and V_c (conduction band minima (CBM)) at almost middle point of Γ and K-point. But monolayer MoS₂ has a direct transition from K_v to K_c point. By decreasing number of layers, band structure of MoS₂ is found to show crucial changes. In the evolution of band structure, K-point remains at the same energy, while Γ point decreases the

energy with decreasing layer number [25]. Such outstanding properties of the band structure of MoS₂ is shown due to different components of electronic states at K point and Γ point. At the K point, electronic states are built up with d-orbital of the Mo atom, which has minimum interlayer coupling. Thus, they do not depend on changed layers. While at Γ point, electronic states are composed by a linear combination of d-orbitals of Mo atom and 3P_z orbital of S atom. Therefore, the strong coupling between neighbour layers is the main cause of downshift of Γ_v point in its energy level [26–28]. Also due to down shift of Γ_v point, VBM changes from Γ_v to K_v point for monolayer. Thus, 3P_z orbitals of S atom plays a crucial role in the transition from indirect to direct bandgap [29]. Valance band maxima shows a large splitting into two bands due to spin-orbit coupling and inversion symmetry in few layers [30].

3.2 Optical property from UV–vis spectrum

In this section, optical properties have been calculated and plotted. When a light energy passes through a medium, some of them may be reflected, some transmitted and some absorbed by medium. The intensity of incident light (I_0) must be equal to the intensity of reflected (I_R), transmitted (I_T) and absorbed ray (I_A) [31].

$$I_0 = I_R + I_A + I_T \quad (1)$$

Dividing equation (1) by I_0 , we get sum of reflectivity (I_R/I_0), absorptivity (I_A/I_0) and transmissivity (I_T/I_0) equal to one [32].

$$R + A + T = 1 \quad (2)$$

Transmittance can be simulated by using Beer's law $T = 10^{-A}$ [33,34]. The parameter of reflectance can also be calculated by following the equation $R = 1 - (A + T)$. The graphical representations of transmittance and reflectance vs. wavelength are shown in figure 3c and d. Reflectance are found to be almost constant (0.2 from 300 to 670 nm). Optical absorption coefficient can be calculated by the relation ($\alpha = 2.303 \times A$), where α is the absorption coefficient. The variation of absorption coefficient vs. wavelength is presented in figure 3a. This is mirror reflection of absorption spectra. The extinction coefficient (K) of the sample is simulated by using the following relation from experimental data [35].

$$K = \frac{\alpha \lambda}{4\pi t} \quad (3)$$

where λ is the wavelength of electromagnetic wave and t is the sample thickness ($t = 1$ cm). The variation of K with wavelength (λ) is illustrated in figure 3f. The values of extinction coefficient lie in between 2.0×10^{-6} to 4.0×10^{-6} and it determines the absorption of electromagnetic energy by the material [36]. Its low value indicates that the medium is transparent. The optical refractive index (n) of the medium is also informative and the key parameter to design optical device, which determines the reduction of the speed of light within the medium [32]. The calculation of refractive index (n) is based on reflection and absorption. Thus, expression of refractive index can be represented in terms of reflectance (R) and extinction (K) of the sample [37–40].

$$n = \left[\frac{1+R}{1-R} \right] + \sqrt{\left[\frac{4 \times R}{(1-R)^2} - K^2 \right]} \quad (4)$$

In figure 3e, the refractive index vs. wavelength graph indicates that, the range of n varies from 0.9 to 2.3. The maximum values of r.i (n) are found to be from 300 to 670 nm. The optical conductivity (σ) of the prepared sample is [41]

$$\sigma = \frac{n\alpha c}{4\pi} \quad (5)$$

where c = speed of light (3×10^{10} m s⁻¹). The graphical plot of the optical conductivity vs. wavelength is exhibited in figure 3b. The maximum value of optical conductivity is found at 260 nm (5.9×10^9 S cm⁻¹) and it shows wavelength-dependent nature and varies from 1.5×10^9 to 6.0×10^9 S cm⁻¹. The optical refractive index (n) and optical dielectric constants are two important physical parameters utilized for delineating optical properties of the medium. The complex dielectric constant ($\epsilon_r = \epsilon_1 + i\epsilon_2$) is also a measure of light absorbed by the medium. The real part and imaginary part of dielectric constant is directly related to the refractive index and extinction coefficient by the relations [41–43].

$$\epsilon_1 = n^2 - K^2 \quad (6)$$

$$\epsilon_2 = 2 \times n \times K \quad (7)$$

When light ray passes through the medium, optical dielectric constant plays an important role since ($n \approx \sqrt{\epsilon_1}$) [41]. The graphical plot of real part (ϵ_1) and imaginary part (ϵ_2) vs. wavelength of electromagnetic wave for MoS₂ nanoflakes is pictorial in figure 3g and h. The values of real part and imaginary part of dielectric constant varies from 0.7 to 4.5 and 5.2×10^{-6} to 1.55×10^{-5} , respectively. The maximum value of ϵ_1 is around 320 and 525 nm while, maximum value of ϵ_2 is at 470 nm.

In our best knowledge, we take first attempt to calculate dielectric constant as well as refractive index of 2D materials MoS₂ directly from absorption spectrum.

3.3 PL spectra of 2D material MoS₂

The PL spectra recorded at room temperature for MoS₂ nanocrystal with excitation wavelength 600 nm is shown in figure 4a. In PL spectra, two prominent peaks are located at 736 and 674 nm due to A and B excitons [44,45]. Emission mechanism for MoS₂ is shown in figure 4b. The broadening peak in the spectra may be due to impurity of the sample. The spin-orbit splitting energy of valance band can be roughly estimated from the peak positions, which is 155 meV. This result tally significantly with the value of 160 meV reported elsewhere for monolayer [46,47]. This splitting energy depends on temperature, because peak position of A and B exciton changes due to temperature. It can be well described by semi-empirical formula based on electron-phonon coupling [49–52]. In this model, exciton energy is

$$E_x^T = E_x^0 - S \langle \hbar\omega \rangle \left[\coth \left(\frac{\langle \hbar\omega \rangle}{K_b T} \right) - 1 \right] \quad (8)$$

where K_B is the Boltzmann constant, E_x^0 is the exciton energy at zero temperature, $\langle \hbar\omega \rangle$ refers to the average energy of phonon, which contributes to the temperature change of excitonic energy and S is the dimensionless

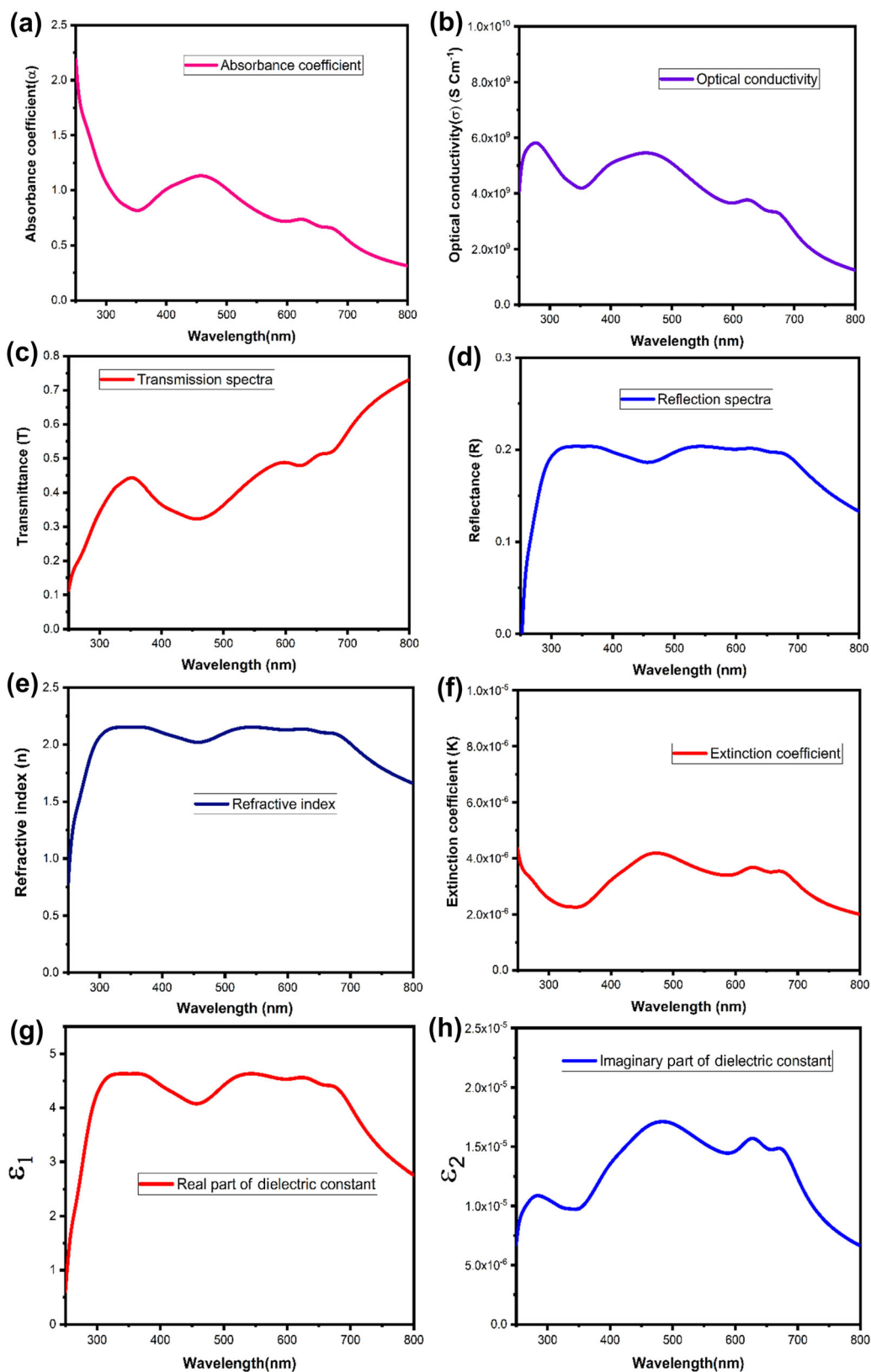


Figure 3. (a) Absorption coefficient vs. wavelength; (b) optical conductivity vs. wavelength; (c) transmittance vs. wavelength; (d) reflectance vs. wavelength; (e) refractive index vs. wavelength; (f) extinction coefficient vs. wavelength; (g) real part of dielectric constant vs. wavelength and (h) imaginary part of dielectric constant vs. wavelength graph.

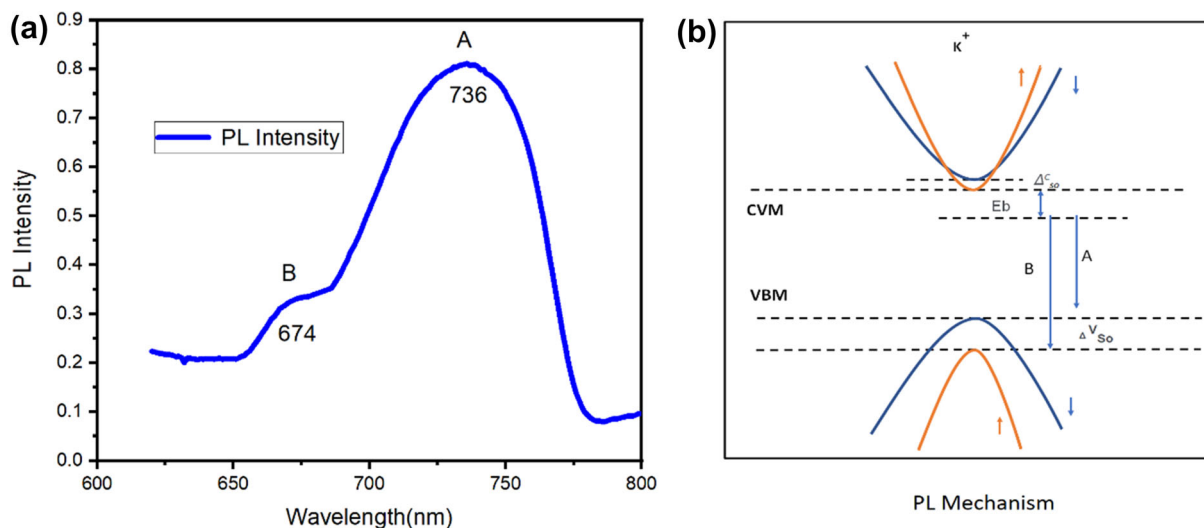


Figure 4. (a) PL spectra of MoS₂, and (b) PL mechanism.

electron–phonon coupling constant. From equation (8) the temperature-dependent exciton energy (E_x) is simulated (different parameters for A and B exciton are shown in table 1) and has been plotted in figure 5a. This result is in good agreement with experimental results as reported for few-layered MoS₂ [48,52]. Also, it can be predicted that splitting energy is almost constant up to 50 K and then it decreases with increase in temperature, as in figure 5b. At higher temperature, the decrease may be due to thermal expansion, small change in bonding length and increase in photon–phonon interaction [51].

3.4 TCSPC study

One of the most excellent experiment time correlated single photons counting (TCSPC) has been investigated for calculating lifetime of the carriers. Here, the sample has been excited at 467 nm using a delta diode laser. The carriers are excited to the higher energy levels and then after certain time they jump to the ground level. The lifetime of carriers is the time measured for the numbers of excited carriers to decay exponentially to 36.8% of the original population. Average lifetime of carriers for MoS₂ sample is found to be 0.75 ns (figure 8a). Ahamed and Neethirajan [53] also determined average lifetime for MoS₂ QD as 0.95 ns].

3.5 XRD study

The XRD patterns of as-prepared powder sample are presented in figure 6a. The diffraction peak is obtained at $2\theta = 14.2^\circ$ indicates that MoS₂ layers stack orderly along [002] direction with d-spacing of 0.614 nm, and other diffraction peaks at 28.32, 33.0, 39.43, 58.69 and 69.26 indexed as (004), (101), (103), (105), (110) and (201) plane, respectively. All the diffraction peaks have been perfectly matched with JCPDS data (JCPDS card no- 01-0872416), which assigns as hexagonal crystal structure with lattice parameters $a = b = 0.316$ nm, and $c = 1.226$ nm. No impurity peaks were observed in the XRD pattern. The approximate crystallite size can be roughly estimated by Debye-Scherrer formula [54].

$$D = \frac{K\lambda}{\beta \cos\theta}, \quad (9)$$

where $K = 0.9$, λ is wavelength of X-ray ($\lambda = 1.5404 \text{ \AA}$). β is the full-width at half-maximum (FWHM) in radian and θ is Bragg angle in radian. Few MoS₂ layers are stacked in the c-direction and the calculated average size of MoS₂ in Z-axis is 2.24 nm (along [002] direction). Thus, prepared powder sample has roughly 3 to 4 layers. Guo *et al* [55] also prepared multilayers MoS₂ and calculated 25 layers from XRD data.

Table 1. Values of different parameters for A and B exciton.

	E_x^0 (calculated)	E_x^{293} (experimental)	$\langle \hbar\omega \rangle$ [48]	S [48]
A Exciton	1.752 eV	1.684 eV	23 meV	2.2
B Exciton	1.923 eV	1.840 eV	16 meV	2.3

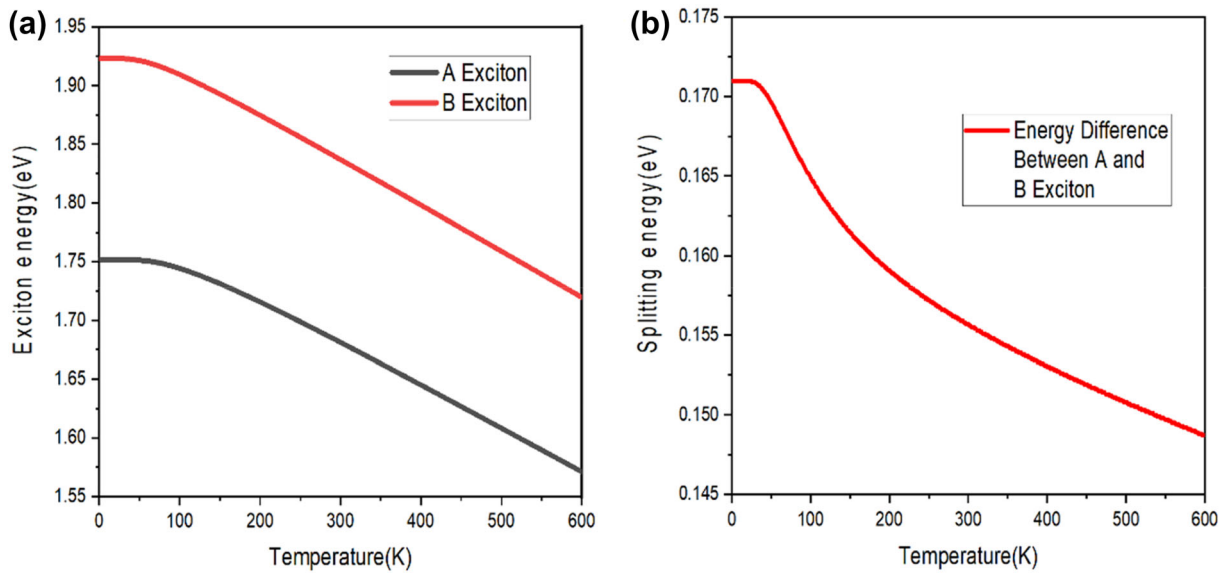


Figure 5. (a) Exciton energy vs. temperature and (b) splitting energy vs. temperature graph.

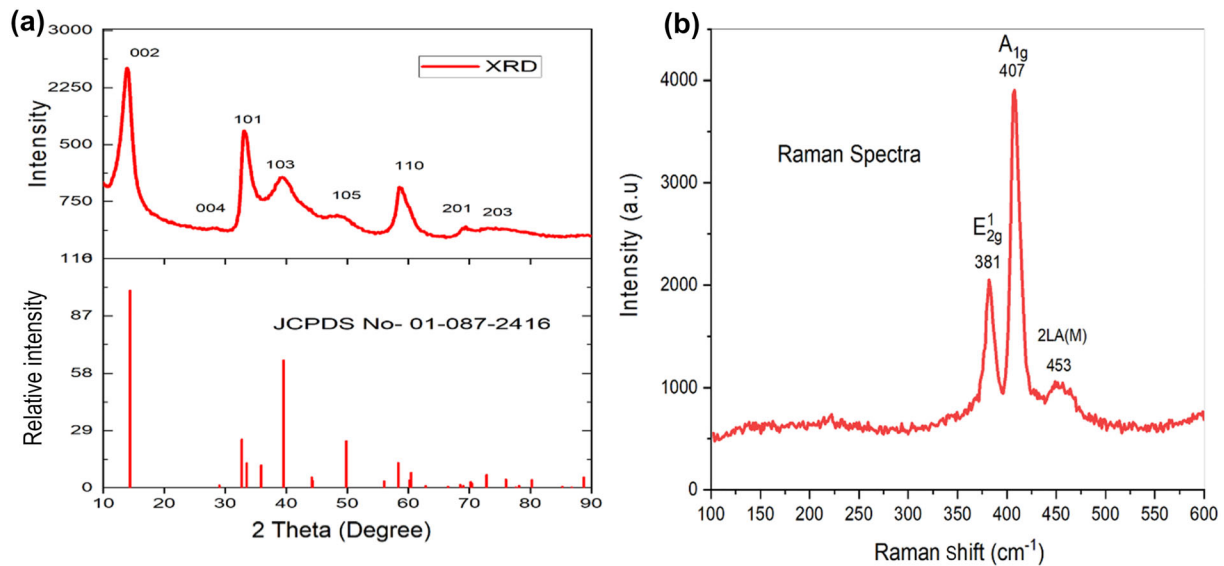


Figure 6. (a) XRD pattern of MoS₂ and (b) Raman spectra of MoS₂.

3.6 Raman spectra

From XRD, it is clear that MoS₂ has hexagonal crystal symmetry and it has P63/mmc space group, and six atoms are contained in its primitive unit cell. Thus, the dispersion relation of 2H-MoS₂ shows 18 branches, among which 15 are optical branches. At the zone centre Γ of the hexagonal Brillouin zone, the irreducible representation of optical phonon modes [25,29] is

$$\begin{aligned} \Gamma_{2H,optical} = & A_{1g}(R) + A_{2u}(IR) + 2B_{2g}(S) + B_{1u}(S) \\ & + E_{1g}(R) + E_{1u}(IR) \\ & + 2E_{2g}(R) + E_{2u}(S), \end{aligned} \quad (10)$$

where R, IR, S mean Raman, infrared and silent modes, respectively. The A_{1g}, A_{2u}, B_{2g}, B_{1u} modes demonstrate atomic displacement of out-of-plane and singly degenerate, while the E_{1u}, E_{1g}, E_{2u} and E_{2g} modes exhibit in-plane displacement and are doubly degenerate [56]. A room temperature Raman spectrum of 2H-MoS₂ nanocrystal is illustrated in figure 6b. The location of the two main peaks are 407 cm⁻¹ (A_{1g}) and 381 cm⁻¹ (E_{2g}¹) in Raman spectra. E_{1g} mode is not noticed because of selection rules. Again, if the filters are not used properly to refuse strong Rayleigh scattering, E_{2g}² mode cannot be resolved [29]. Another broad peak at 453 cm⁻¹ is denoted as 2LA(M), assigned as second-order overtone of longitudinal acoustic phonon at

the M-point of the Brillouin zone. It may be due to 1H-MoS₂ phase [29].

3.7 Morphology study by HRTEM

HRTEM results for the exfoliated sample by probe sonicate, as shown in figure 7, indicate that the sample has a nano-sheet structure in irregular shapes. HRTEM is a common and direct method to determine the number of layers microscopically [57]. Here, three-layer nano-sheet are

found in the HRTEM, which agrees with XRD result. Fei *et al* [58] also observed that MoS₂ stacks 4–5 layers in vertical direction for low growth temperature. From figure 7c, measured inter-planar spacing 0.58 nm corresponds to (002) plane. Figure 7b manifests that MoS₂ has hexagonal crystal symmetry, which is supported by the XRD result. Also, figure 7d indicates that MoS₂ has a nano-flake structure and average size of nano-flake is 100 nm. Selected area electron diffraction (SAED) are shown in figure 7a. Here, rings appeared due to different crystal planes and these can be indexed using JCPDS data by

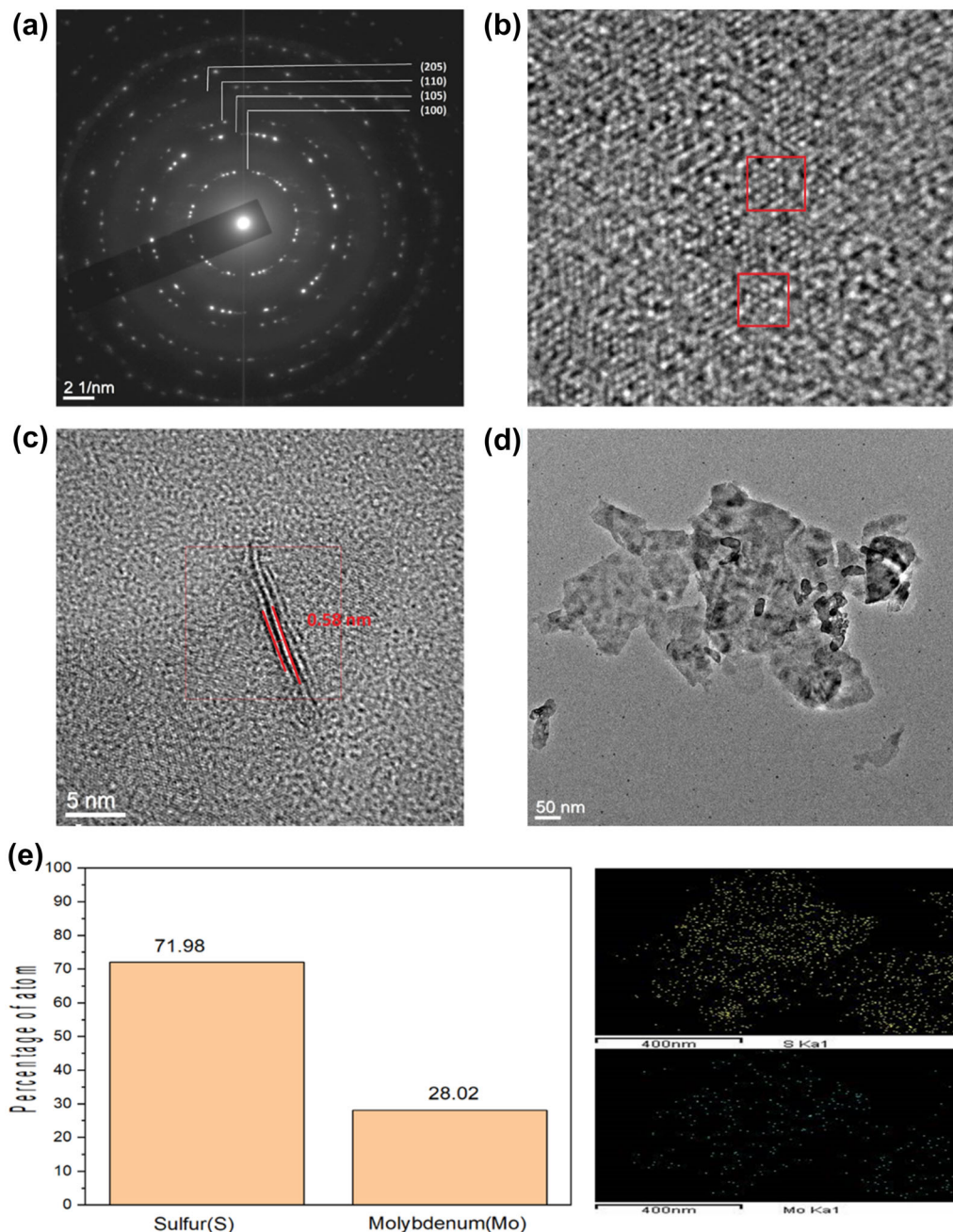


Figure 7. (a) SAED of MoS₂; (b) hexagonal crystal structure; (c) three layers MoS₂; (d) nano-flake of MoS₂ and (e) composition of molybdenum (Mo) and sulphur (S).

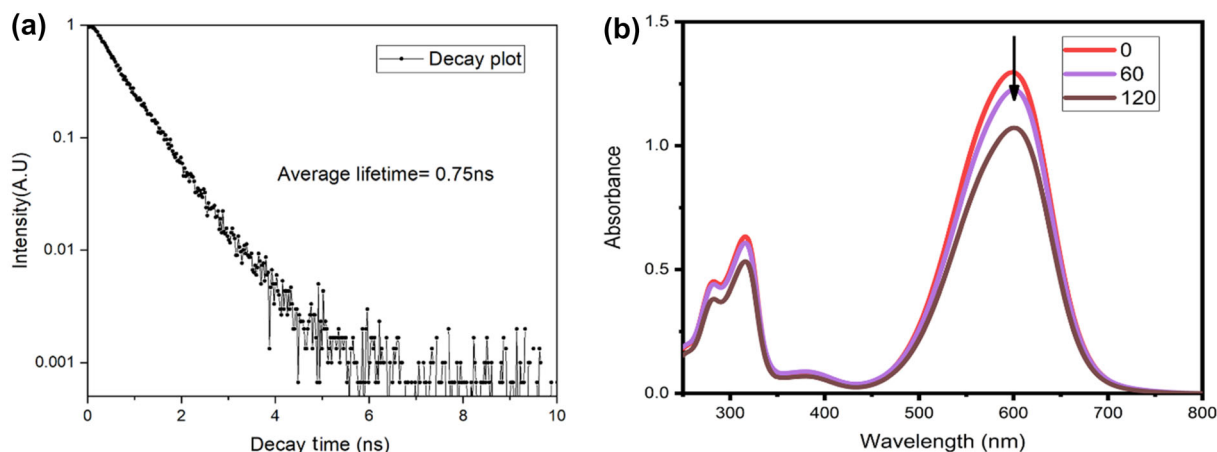


Figure 8. (a) Decay plot of MoS₂ and (b) MB dye degradation.

ImageJ software. Composition of Mo and S are found from HRTEM result, which is shown in figure 7e by histogram plot.

4. Photocatalytic activity

In order to investigate the photocatalytic performance of prepared sample, UV-Vis-NIR spectrometer has been used. At first, dye solution (2 mg in 50 ml) and the nanomaterial solution (3 mg in 10 ml) have been prepared with distilled water. Then, two solutions were mixed under dark condition and kept for 30 min without irradiation in order to obtain equilibrium of dye adsorption. After that, the solution was irradiated under the light (approximate light intensity 0.75 Wm⁻²). After light is ON, absorption spectra are recorded under 60-min time interval, which is shown in figure 8b. Down-shift of peak position clearly indicates that MB dye has been degraded.

5. Conclusion

In summary, crystalline 2H-MoS₂ has been synthesized by hydrothermal method. To investigate optical and structural properties, absorption spectra, PL spectra, TCSPC, XRD, Raman and HRTEM have been performed and explained with appropriate mechanism. Dielectric constant as well as refractive index is calculated from experimental data. Simulated splitting energy of valance band are dependent on temperature. The calculated excitonic energy agrees well with the available electron-phonon coupling theory. Exfoliated MoS₂ has three-layers, which is suitable for different applications. For photocatalytic activity of MB dye degradation, activity depends directly on concentration of nanomaterials.

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